

Silicon NPN Power Transistors

2SD817

DESCRIPTION

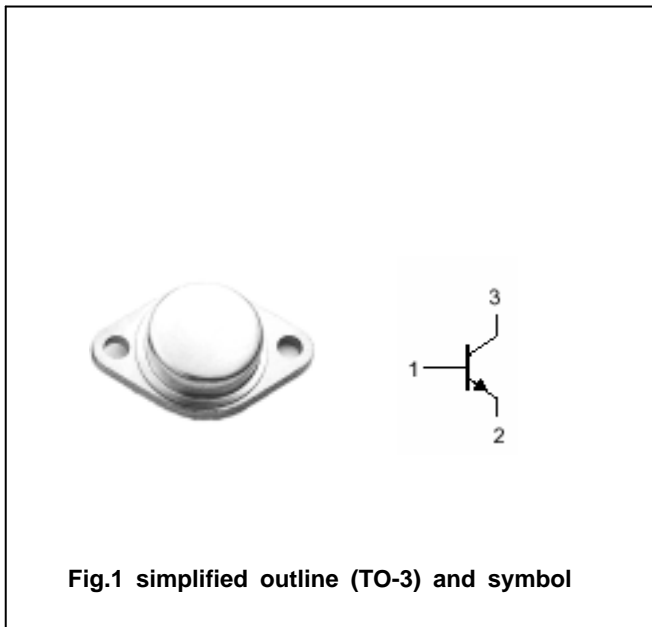
- With TO-3 package
- High voltage ,high reliability
- Wide area of safe operation

APPLICATIONS

- High voltage power switching TV horizontal deflection output applications

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Absolute maximum ratings(Ta=)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{CEO}	Collector-emitter voltage	Open base	600	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		1.5	A
P_C	Collector power dissipation	$T_C=25$	50	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA; I _C =0	6			V
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =10mA; I _B =0	600			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =1.2A; I _B =0.3A			5.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =1.2A; I _B =0.3A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =800V; I _E =0			10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =6V; I _C =0			10	μA
h _{FE}	DC current gain	I _C =0.3A; V _{CE} =5V	10		30	

固电半导体
INCHANGE SEMICONDUCTOR

PACKAGE OUTLINE

